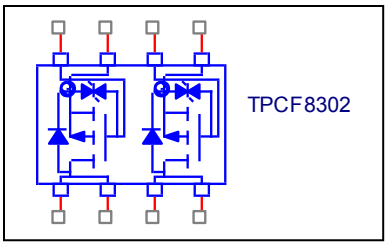
Device Modeling Report

COMPONENTS: Power MOSFET (Standard)
PART NUMBER: TPCF8302
MANUFACTURER: TOSHIBA
Body Diode (Standard) / ESD Protection Diode

Bee Technologies Inc.

Circuit Configuration

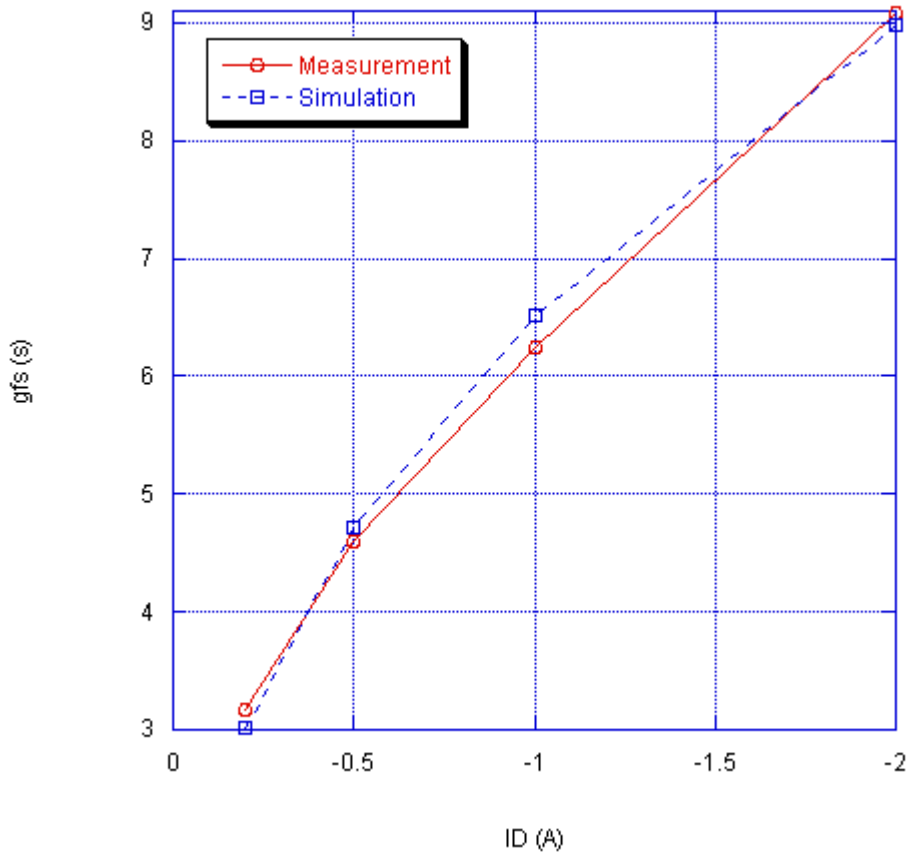


MOSFET MODEL

PSpice model parameter	Model description
LEVEL	
L	Channel Length
W	Channel Width
KP	Transconductance
RS	Source Ohmic Resistance
RD	Ohmic Drain Resistance
VTO	Zero-bias Threshold Voltage
RDS	Drain-Source Shunt Resistance
TOX	Gate Oxide Thickness
CGSO	Zero-bias Gate-Source Capacitance
CGDO	Zero-bias Gate-Drain Capacitance
CBD	Zero-bias Bulk-Drain Junction Capacitance
MJ	Bulk Junction Grading Coefficient
PB	Bulk Junction Potential
FC	Bulk Junction Forward-bias Capacitance Coefficient
RG	Gate Ohmic Resistance
IS	Bulk Junction Saturation Current
N	Bulk Junction Emission Coefficient
RB	Bulk Series Resistance
PHI	Surface Inversion Potential
GAMMA	Body-effect Parameter
DELTA	Width effect on Threshold Voltage
ETA	Static Feedback on Threshold Voltage
THETA	Mobility Modulation
KAPPA	Saturation Field Factor
VMAX	Maximum Drift Velocity of Carriers
XJ	Metallurgical Junction Depth
UO	Surface Mobility

Transconductance Characteristic

Circuit Simulation Result

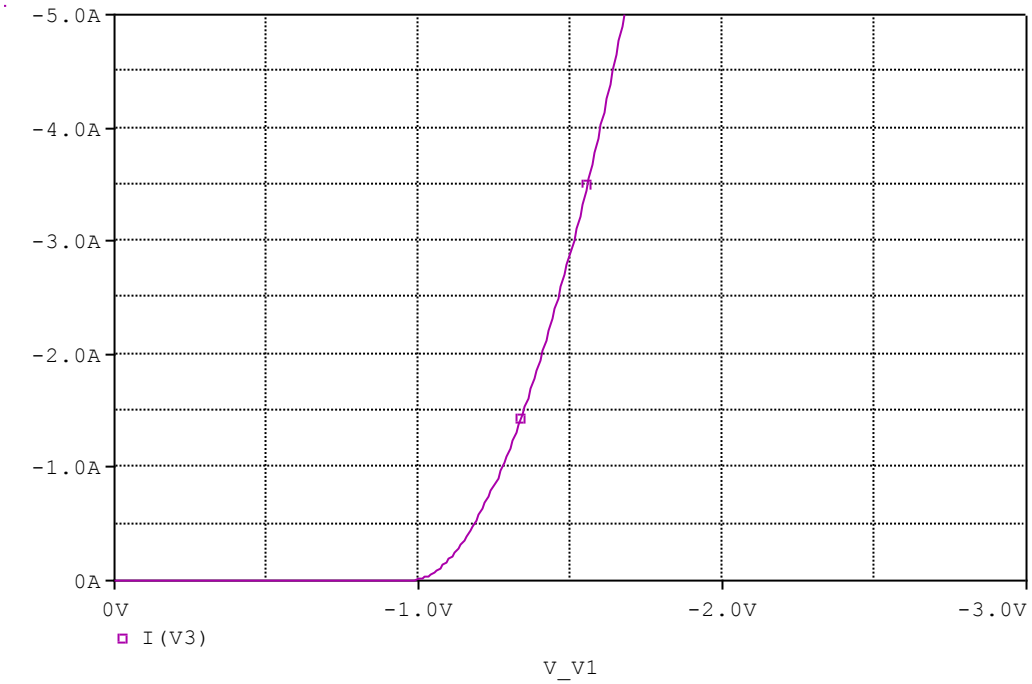


Simulation Result

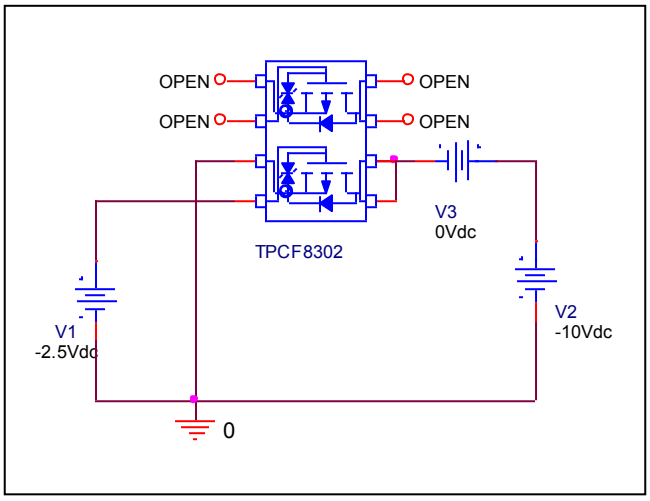
I_D(A)	V_{GS}(V)		Error (%)
	Measurement	Simulation	
-0.200	3.170	3.017	-4.826
-0.500	4.600	4.717	2.543
-1.000	6.250	6.519	4.304
-2.000	9.090	8.980	-1.210

Vgs-Id Characteristic

Circuit Simulation result

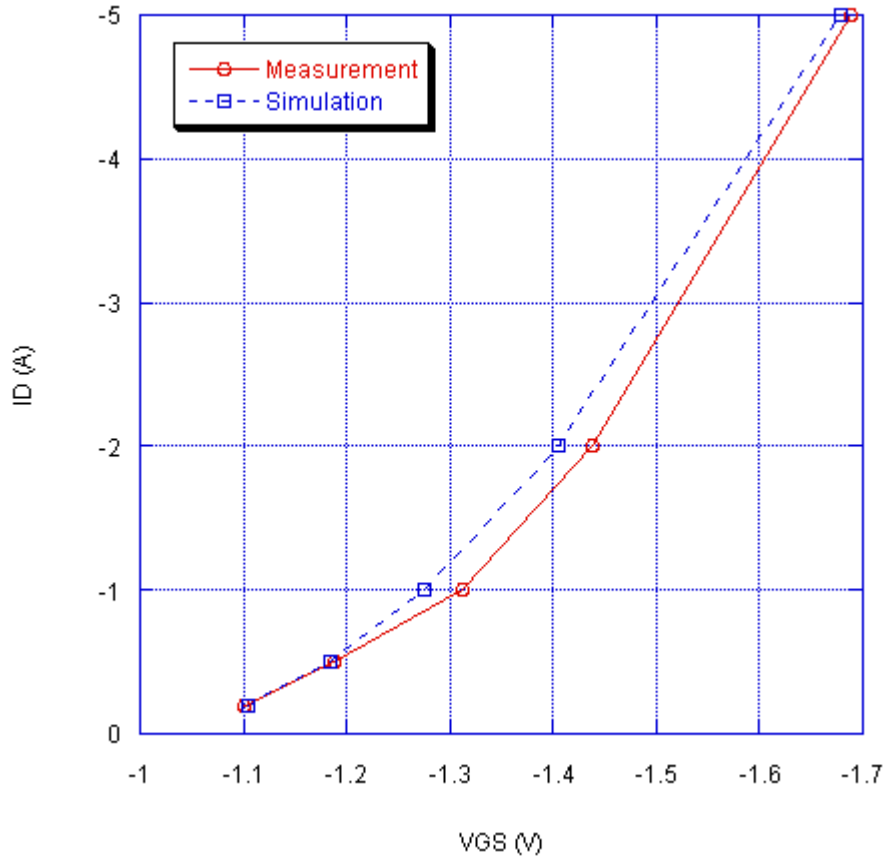


Evaluation circuit



Comparison Graph

Circuit Simulation Result

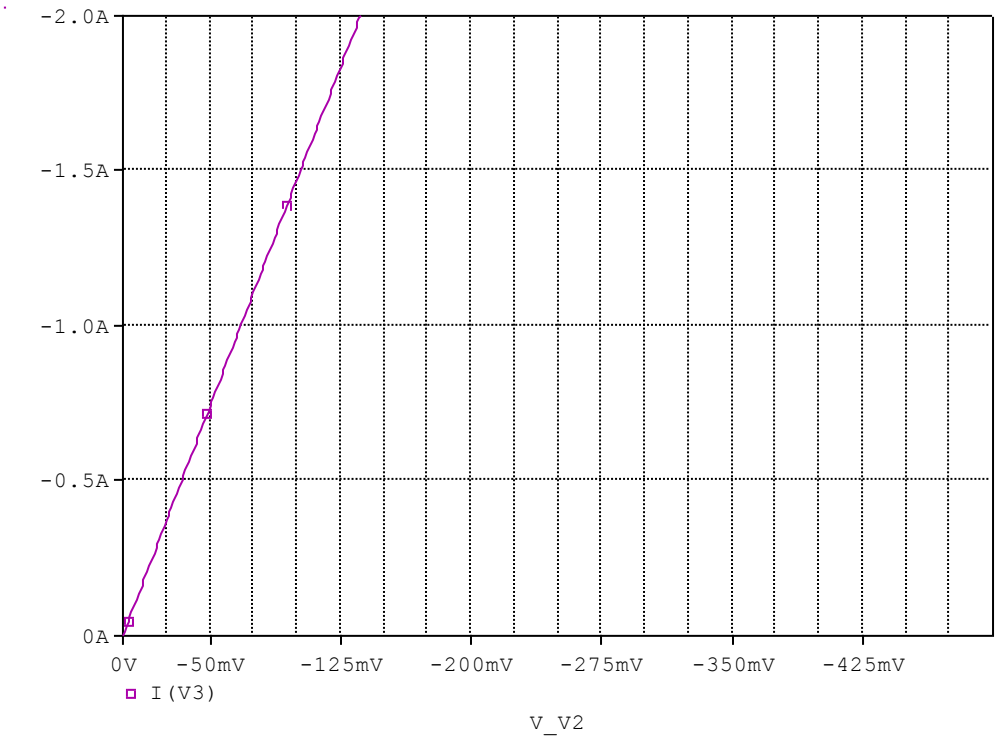


Simulation Result

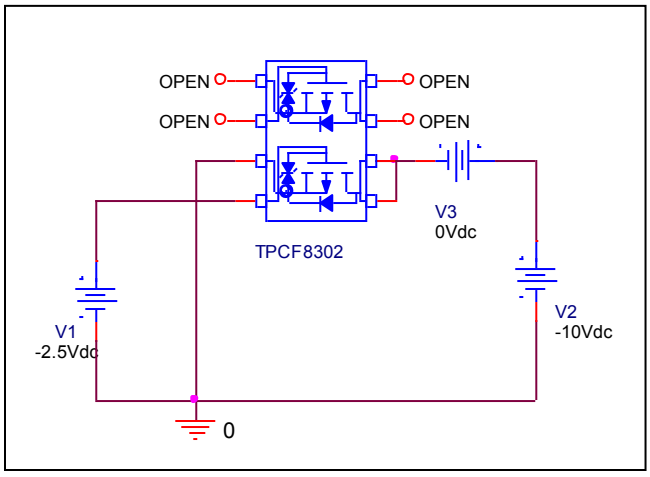
I_D(A)	V_{GS}(V)		Error (%)
	Measurement	Simulation	
-0.200	-1.100	-1.105	0.427
-0.500	-1.188	-1.184	-0.320
-1.000	-1.313	-1.275	-2.895
-2.000	-1.438	-1.406	-2.191
-5.000	-1.688	-1.678	-0.575

Id-Rds(on) Characteristic

Circuit Simulation result



Evaluation circuit

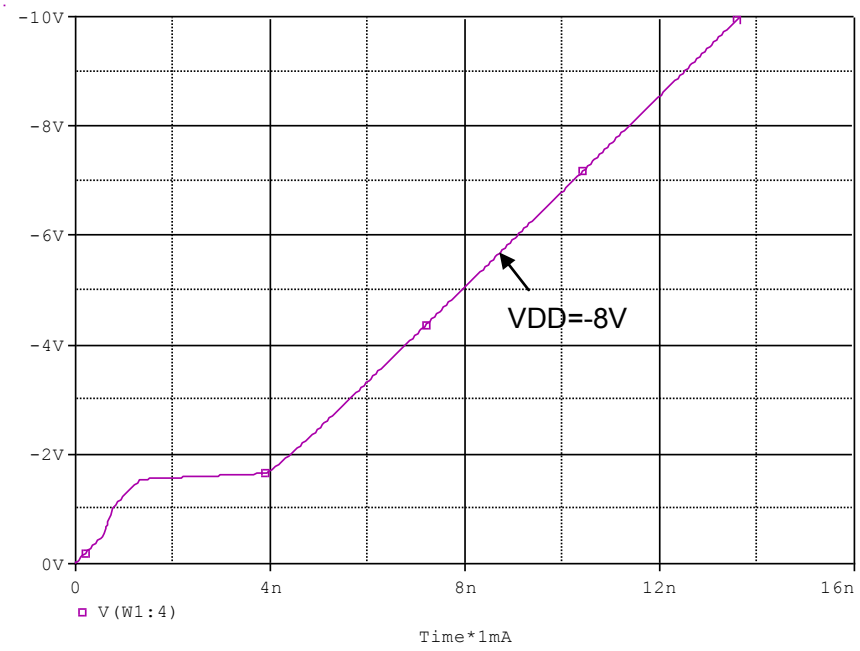


Simulation Result

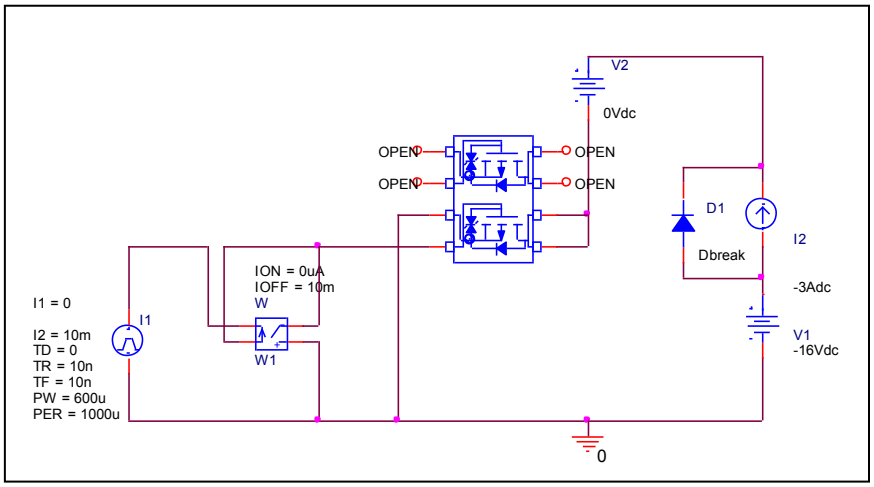
I_D=-1.5, V_{GS}=-2.5V	Measurement		Simulation		Error (%)
R_{DS} (on)	68	mΩ	68	mΩ	0

Gate Charge Characteristic

Circuit Simulation result



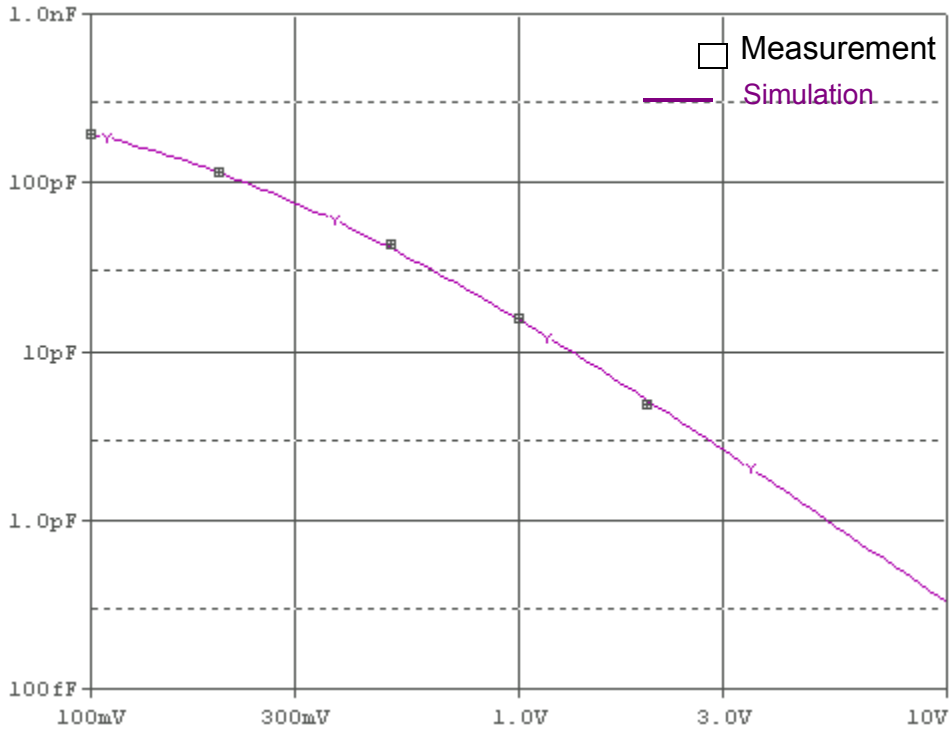
Evaluation circuit



Simulation Result

V_{DD}=-8V,I_D=-3A ,V_{GS}=-5V	Measurement		Simulation		Error (%)
Qgs	1.30	nC	1.313	nC	1.00
Qgd	2.60	nC	2.602	nC	0.08
Qg	9.50	nC	7.930	nC	-16.53

Capacitance Characteristic

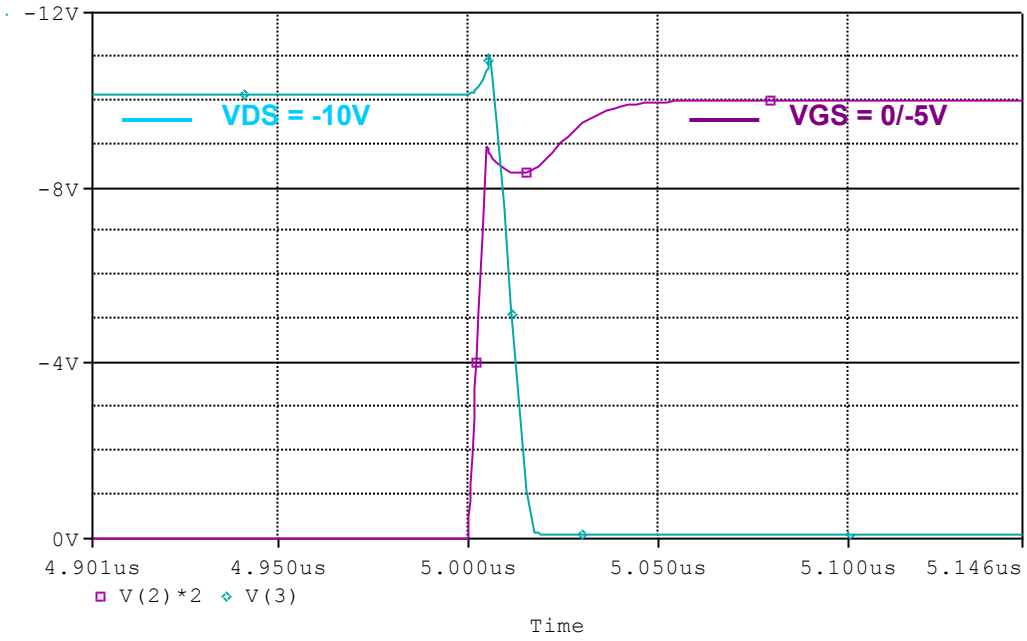


Simulation Result

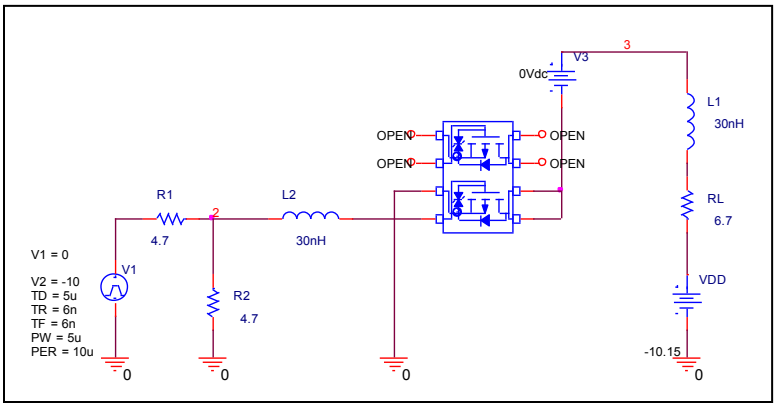
V_{DS}(V)	Cbd(pF)		Error(%)
	Measurement	Simulation	
0.100	200.000	194.000	-3.000
0.200	120.000	117.000	-2.500
0.500	44.000	42.000	-4.545
1.000	16.000	16.000	0.000
2.000	5.000	5.200	4.000

Switching Time Characteristic

Circuit Simulation result



Evaluation circuit

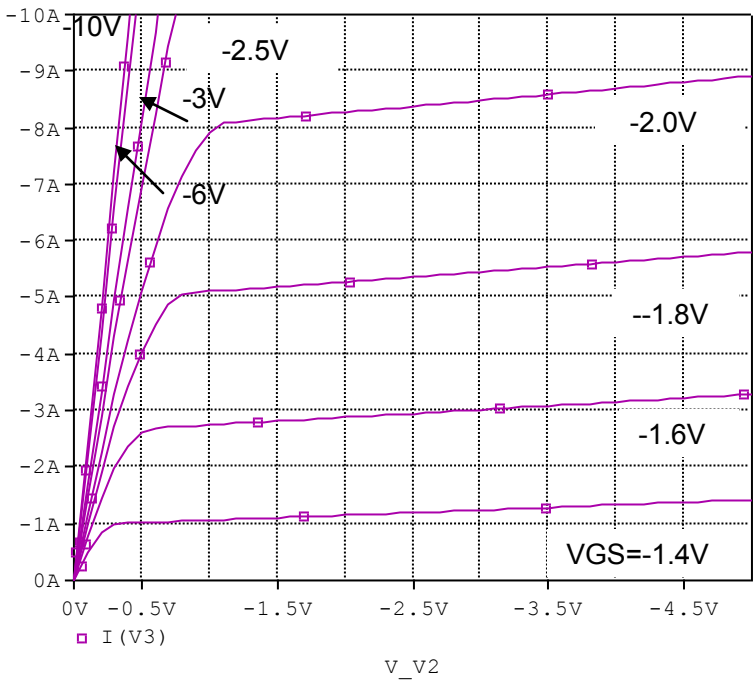


Simulation Result

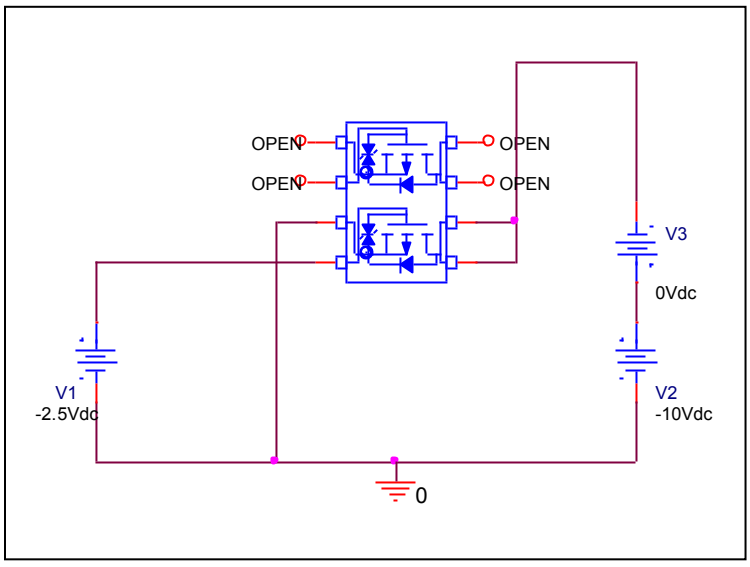
I_D=-1.5A, V_{DD}=-10V V_{GS}=0/-5V	Measurement		Simulation		Error(%)
ton	15.000	ns	15.012	ns	0.080

Output Characteristic

Circuit Simulation result

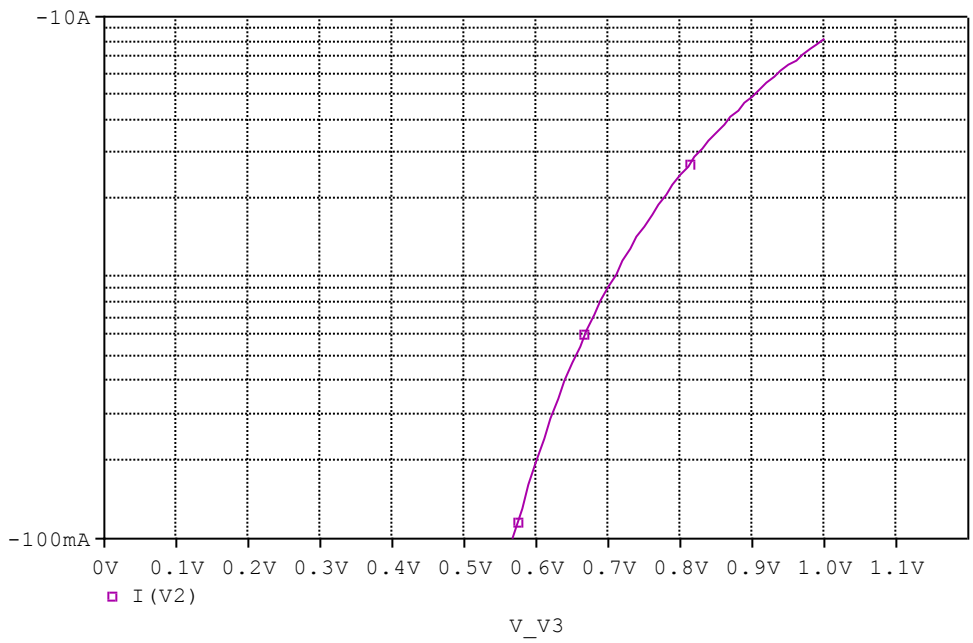


Evaluation circuit

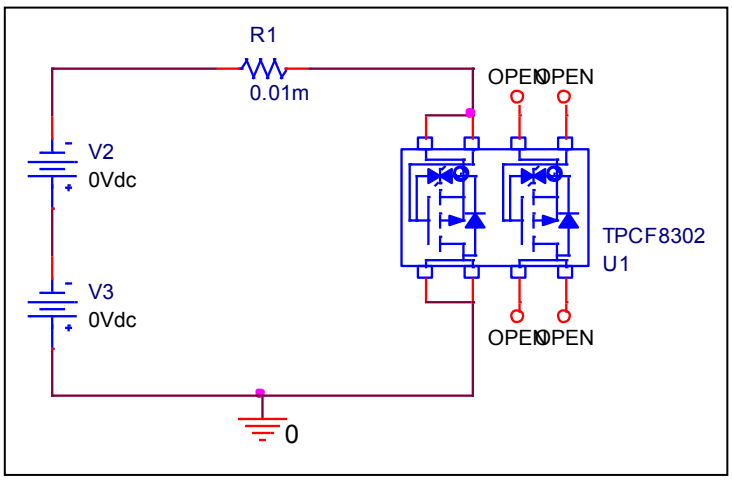


Forward Current Characteristic

Circuit Simulation Result

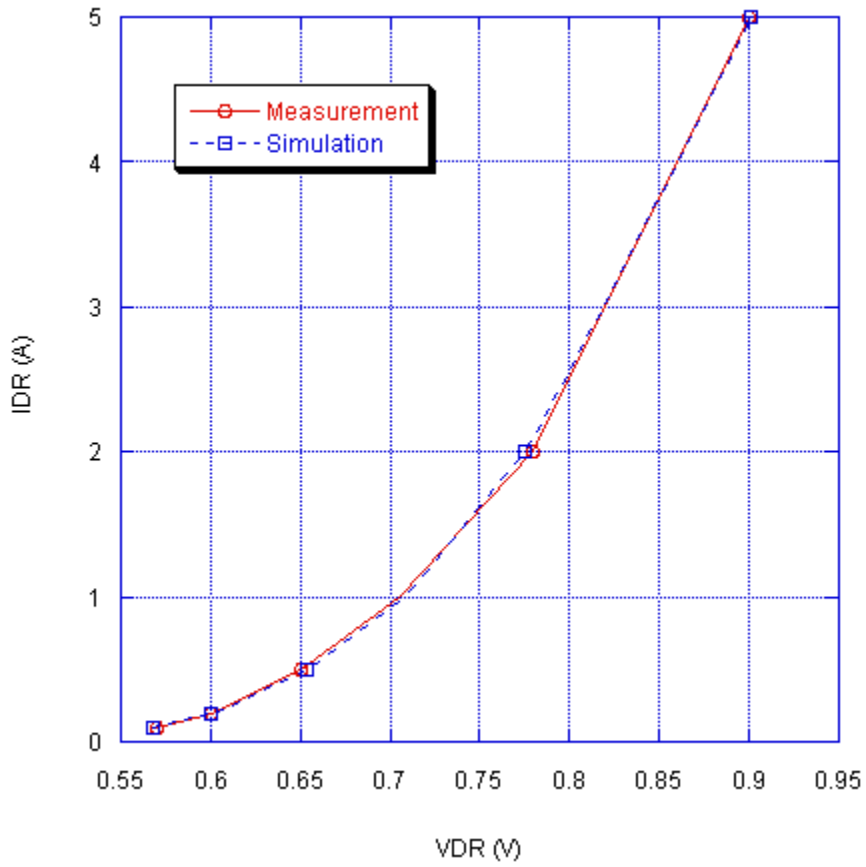


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

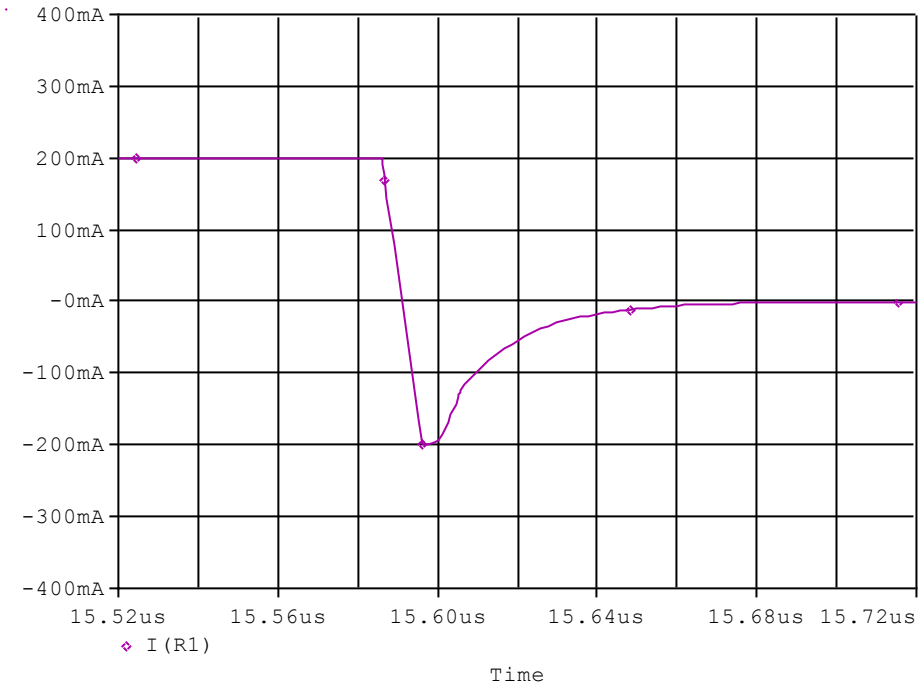


Simulation Result

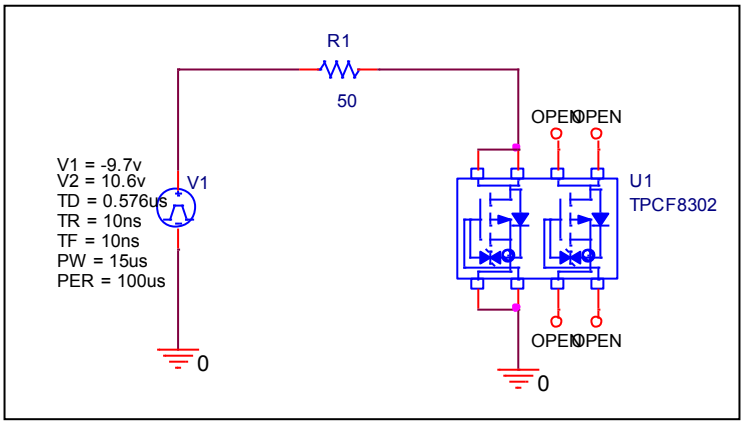
Ifwd(A)	Vfwd(V) Measurement	Vfwd(V) Simulation	%Error
0.100	0.570	0.568	-0.439
0.200	0.600	0.600	0.050
0.500	0.650	0.654	0.569
1.000	0.705	0.707	0.270
2.000	0.780	0.775	-0.641
5.000	0.900	0.901	0.133

Reverse Recovery Characteristic

Circuit Simulation Result



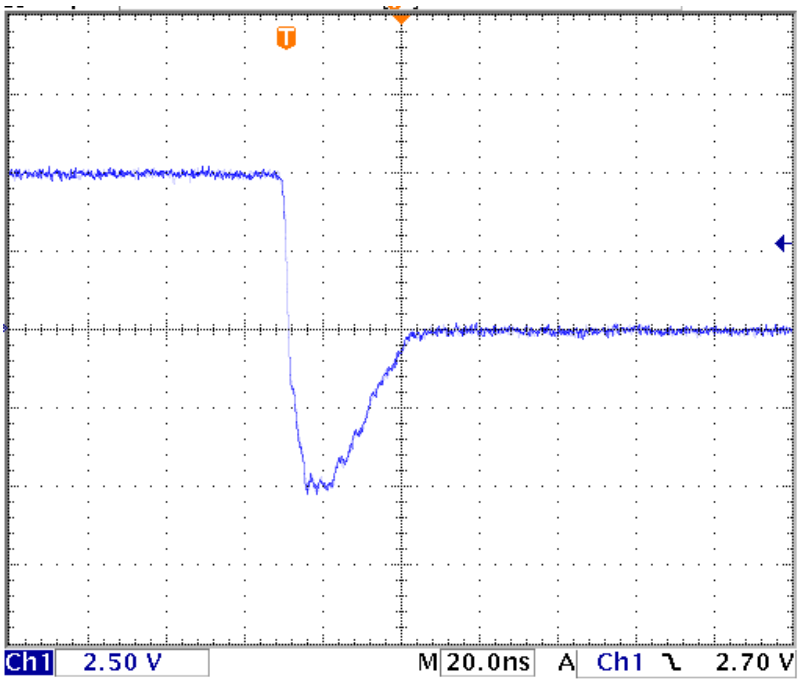
Evaluation Circuit



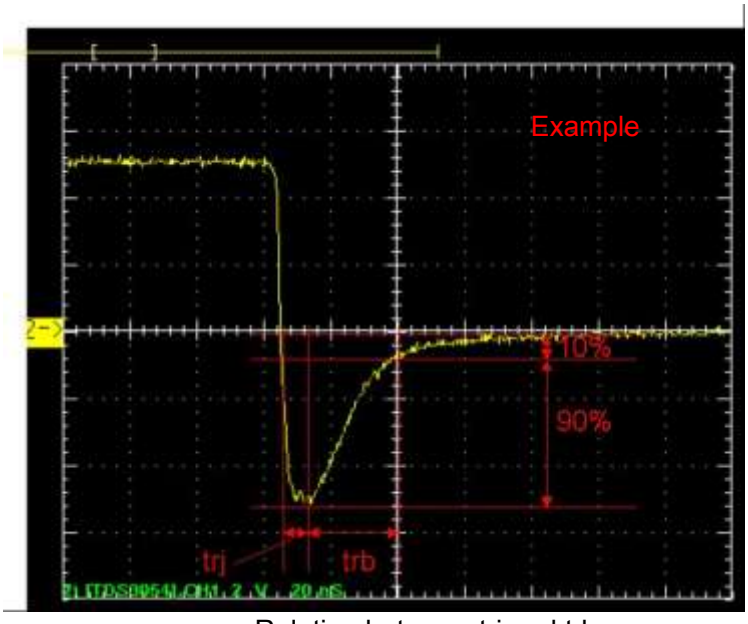
Compare Measurement vs. Simulation

	Measurement		Simulation		Error(%)
trj	4.500	ns	4.677	ns	3.93

Reverse Recovery Characteristic Reference



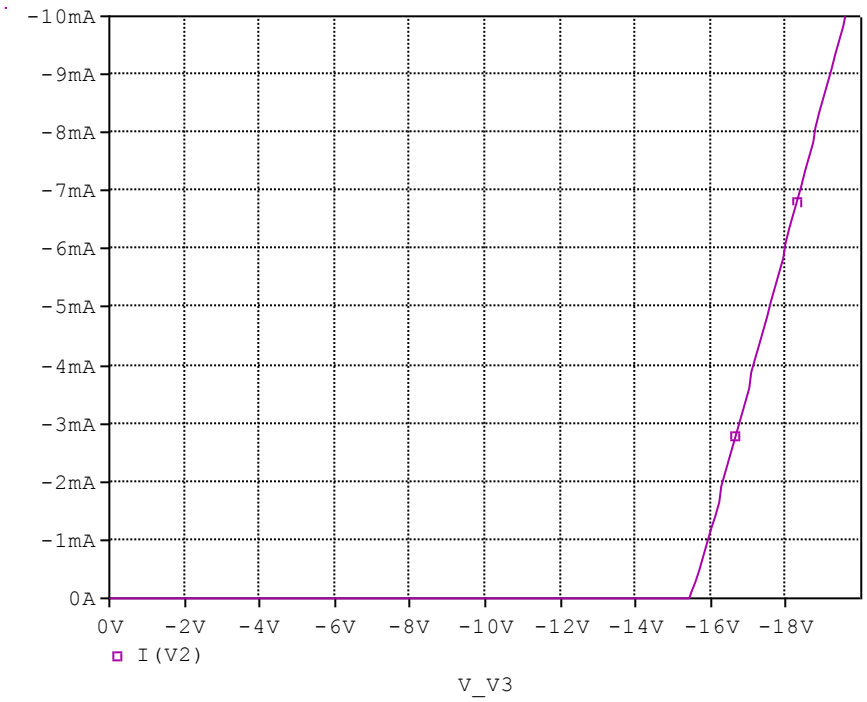
Trj=4.0(ns)
Trb=19.6(ns)
Conditions:Ifwd=Irev=0.2(A),Rl=50



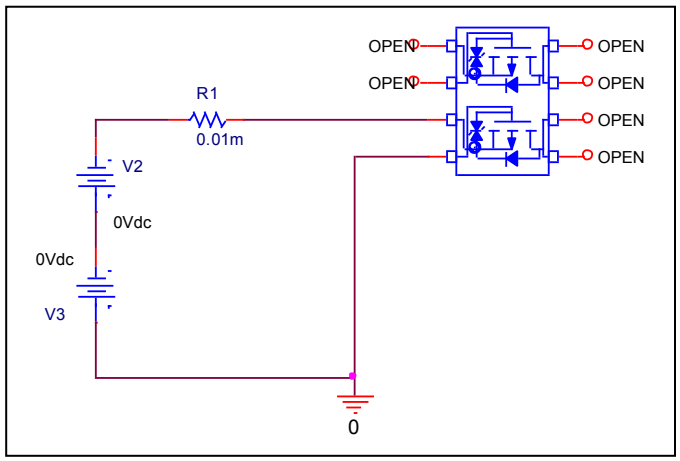
Relation between trj and trb

ESD PROTECTION DIODE SPICE MODEL
Zener Voltage Characteristic

Circuit Simulation Result



Evaluation Circuit



Zener Voltage Characteristic Reference